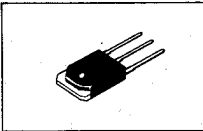




No.1267

2SD1400



NPN Triple Diffused Planar Type Silicon Transistor
FOR CTV HORIZONTAL DEFLECTION OUTPUT

Features:

- High breakdown voltage and high reliability
- High switching speed
- Capable of being mounted easily due to one-point fixing type plastic mold package

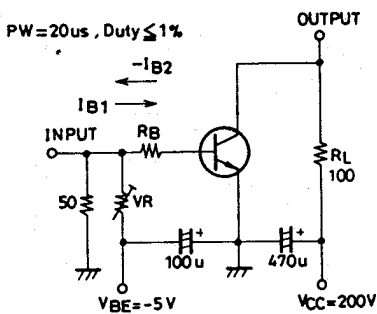
Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	VCBO	1500	V
Collector to Emitter Voltage	VCEO	800	V
Emitter to Base Voltage	VEBO	7	V
Collector Current	IC	2.5	A
Peak Collector Current	icp	10	A
Collector Dissipation	PC	80	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

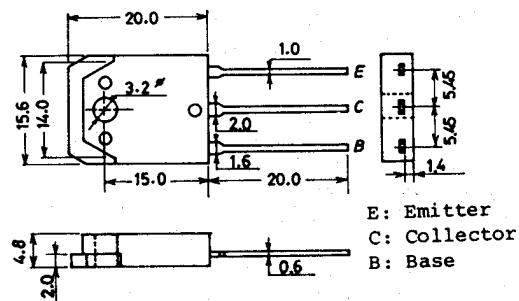
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	ICBO	VCB=800V, IE=0			10	uA
Emitter Cutoff Current	IEBO	VEB=5V, IC=0			1	mA
DC Current Gain	hFE	VCE=5V, IC=0.5A	8			
Gain Bandwidth Product	fT	VCE=10V, IC=0.5A		3		MHz
C-E Saturation Voltage	VCE(sat)	IC=2A, IB=0.6A			8	V
B-E Saturation Voltage	VBE(sat)	IC=2A, IB=0.6A			1.5	V
C-B Breakdown Voltage	V(BR)CBO	IC=5mA, IE=0	1500			V
C-E Breakdown Voltage	V(BR)CEO	IC=100mA, RBE=∞	800			V
E-B Breakdown Voltage	V(BR)EBO	IE=200mA, IC=0	7			V
Fall Time	tf	IC=2A, IB1=0, 6A, IB2=-1.2A			0.7	us

Switching Time Test Circuit



Case Outline 2022 (unit:mm)



These specifications are subject to change without notice.

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